WSB5524D

Middle Power Schottky Barrier Diode **Http://www.sh-willsemi.com**

Features

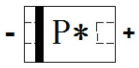
- 1.5A Average rectified forward current
- Low forward voltage,Low leakage current
- FBP package

FBP1608-02L

Circuit

Applications

- Switching circuit
- Middle current rectification



Marking

Absolute maximum ratings

Parameter	Symbol	Value	Unit
Reverse voltage (repetitive peak)	V_{RRM}	40	V
Reverse voltage (DC)	V_R	40	V
Average forward current(1)	$I_{F(AV)}$	1.5	A
Forward Peak Surge Current (2)	I_{FSM}	7	A
Junction temperature	T_J	125	°C
Operating temperature	Topr	-40 ~ 125	°C
Storage temperature	Tstg	-55 ~ 150	°C

Electronics characteristics (T_A=25°C)

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Forward voltage (3)	V_F	I_F=1.5A		0.50	0.60	V
Reverse current	I_R	V_R=40V			0.1	mA
Junction capacitance	C_J	V_R=4V, F=1MHz		57	70	pF
Thermal resistance	$R_{\theta(J-SP)}$	Junction to soldering point of cathode tab			20	K/W

Order Informations

Device	Package	Marking	Shipping
WSB5524D-2/TR	FBP1608-02L(1.6*0.8)	P* (4)	10000/Reel&Tape

Note1: Duty cycle=0.5,f=20kHz,square wave;

Note2: Pulse width=8.3ms, single pulse;

Note3: Single Pulse, test Tp=380us;

Note4: * = Month code (A~Z); P = Device code;

Typical characteristics (Ta=25°C, unless otherwise noted)

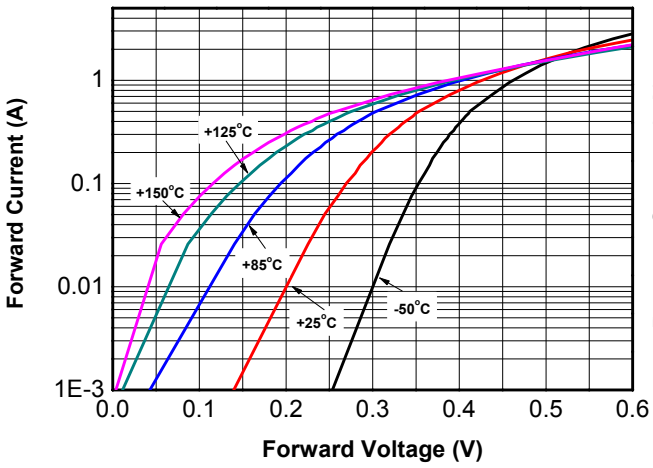


Fig.1 Forward voltage vs. Forward current

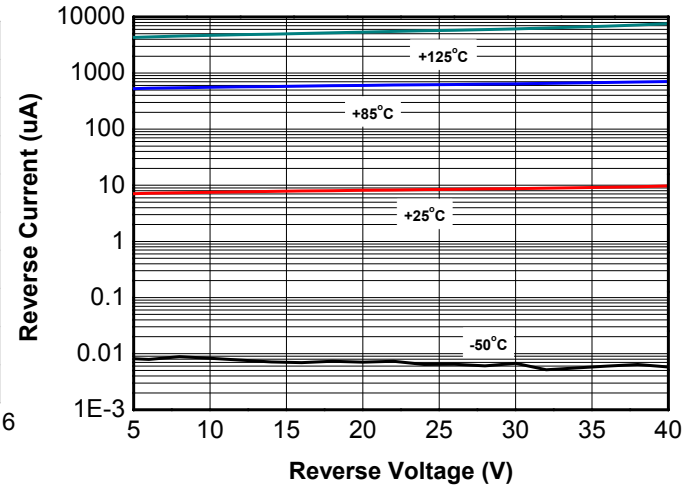


Fig.2 Reverse current vs. Reverse voltage

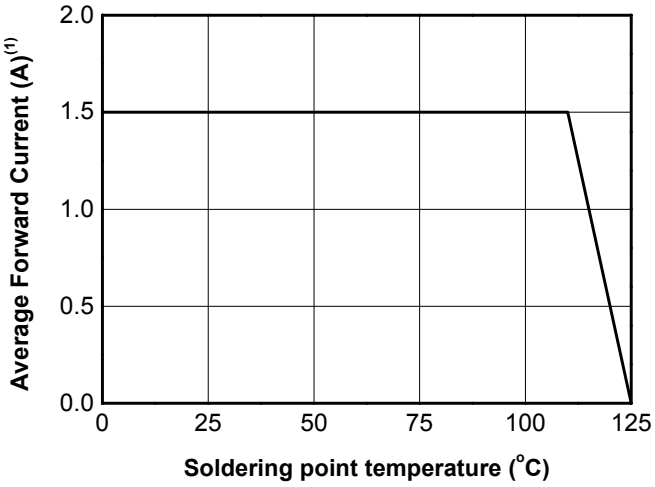


Fig.3 Average Forward Current Derating Curve

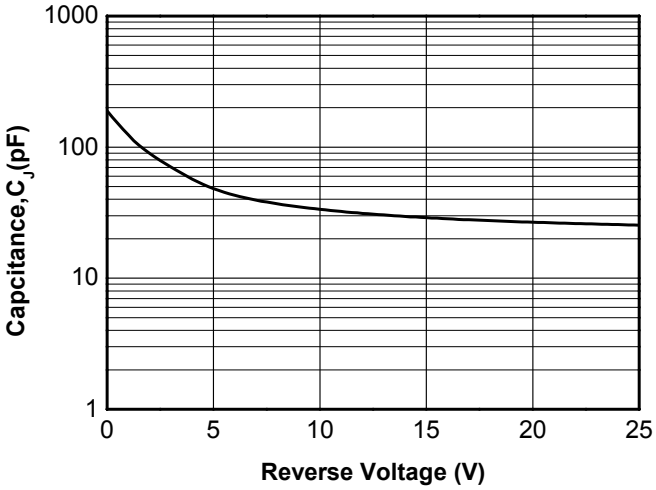
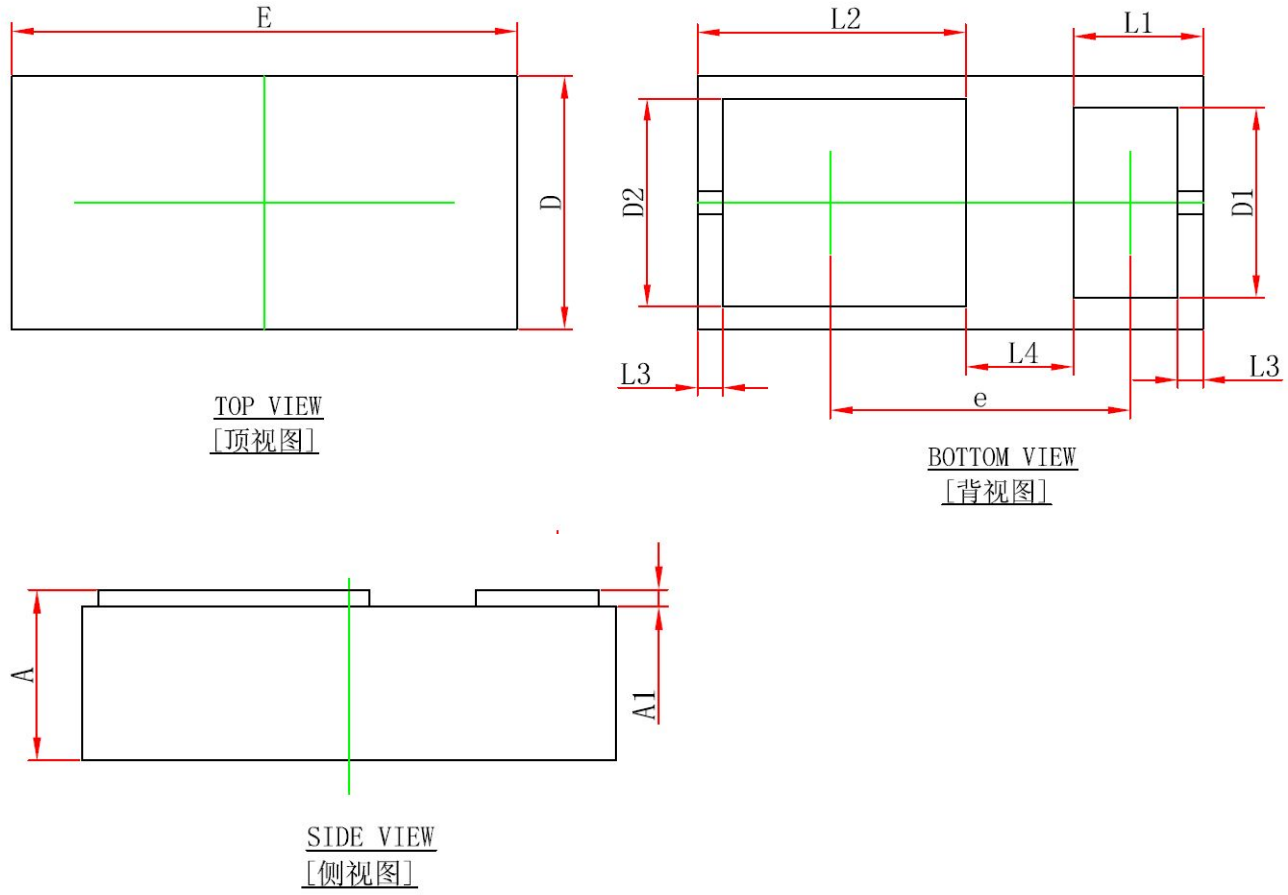


Fig.4 Junction capacitance vs. Reverse voltage

Package outline dimensions

FBP1608-02L(1.6*0.8*0.5)



Symbol	Dimensions In Milimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.450	0.550	0.018	0.022
A1	0.010	0.090	0.000	0.004
D	0.750	0.850	0.030	0.033
D1	0.520	0.680	0.020	0.027
D2	0.600	0.760	0.024	0.030
E	1.550	1.650	0.061	0.065
L1	0.410 REF.		0.016 REF.	
L2	0.850 REF.		0.033 REF.	
L3	0.080 REF.		0.003 REF.	
L4	0.340 REF.		0.013 REF.	
e	0.900	1.000	0.035	0.039